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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



VYBRIDRSERIESEC

VF3xxR, VF5xxR

Features

- Operating characteristics
 - Voltage range 3 V to 3.6 V
 - Temperature range(ambient) -40 °C to 85 °C
- ARM® Cortex® A5 Core features
 - Up to 400 MHz ARM® Cortex® A5 core
 - 32 KB/32 KB I/D L1 Cache
 - 1.6 DMIPS/MHz based on ARMv7 architecture
 - NEON™ MPE (Media Processing Engine) Co-processor
 - Double Precision Floating Point Unit
 - 512 KB L2 cache (on selected part numbers only)
- ARM Cortex M4 Core features
 - Up to 133 MHz ARM Cortex M4
 - Integrated DSP capability
 - 64 KB Tightly Coupled Memory (TCM)
 - 16 KB/16 KB I/D L1 Cache
 - 1.25 DMIPS/MHz based on ARMv7 architecture
- Clocks
 - 24 MHz crystal oscillator
 - 32 kHz crystal oscillator
 - Internal reference clocks (128 KHz and 24 MHz)
 - Phase Locked Loops (PLLs)
 - Low Jitter Digital PLLs
- System debug, protection, and power management
 - Various stop, wait, and run modes to provide low power based on application needs
 - Peripheral clock enable register can disable clocks to unused modules, thereby reducing currents
 - Low voltage warning and detect with selectable trip points
 - Illegal opcode and illegal address detection with programmable reset or processor exception response
 - Hardware CRC module to support fast cyclic redundancy checks (CRC)
 - 128-bit unique chip identifier
 - Hardware watchdog
 - External Watchdog Monitor (EWM)
 - Dual DMA controller with 32 channels (with DMAMUX)
- Debug
 - Standard JTAG
 - 16-bit Trace port
- Timers
 - Motor control/general purpose timer (FTM)
 - Periodic Interrupt Timers (PITs)
 - Low-power timer (LPTMR0)
 - IEEE 1588 Timer per MAC interface (part of Ethernet Subsystem)
- Communications
 - Six Universal asynchronous receivers/transmitters (UART)/Serial communications interface (SCI) with LIN, ISO7816, IrDA, and hardware flow control
 - Four Deserial Serial peripheral interface (DSPI)
 - Four Inter-Integrated Circuit (I2C) with SMBUS support
 - Dual USB OTG Controller + PHY
 - Dual 4/8 bit Secure Digital Host controller
 - Local Media Bus (MLB50)
 - Dual 10/100 Ethernet (IEEE 1588)
 - Dual FlexCAN3
- Security
 - ARM TrustZone including the TZ architecture
 - Secure Non-Volatile Storage (SNVS)
 - Real Time Clock
 - Real Time Integrity Checker (RTIC)
 - TrustZone Watchdog (TZ WDOG)
 - Trust Zone Address Space Controller
 - Random Number Generator
 - Hashing
 - Secure JTAG
- Memory Interfaces
 - 8/16-bit DRAM Controller with support for LPDDR2/DDR3 - Up to 400 MHz (ECC supported for 8-bit only and not 16-bit)
 - 8/16-bit NAND Flash controller with ECC (ECC supported for 8-bit only and not 16-bit)
 - Dual Quad SPI with XIP (Execute-In-Place)
 - 8/16/32-bit External bus (Flexbus)

Freescale reserves the right to change the detail specifications as may be required to permit improvements in the design of its products.

- Display and Video
 - Dual Display Control Unit (DCU) with support for color TFT display up to WVGA
 - Segmented LCD (3V Glass only) configurable as 40x4, 38x8, and 36x6
 - Video Interface Unit (VIU) for camera
 - Open VG Graphics Processing Unit (GPU)
 - VideoADC
- Analog
 - Dual 12-bit SAR ADC with 1MS/s
 - Dual 12-bit DAC
- Audio
 - Four Synchronous Audio Interface (SAI)
 - Enhanced Serial Audio Interface (ESAI)
 - Sony Philips Digital Interface (SPDIF), Rx and Tx
 - Asynchronous Sample Rate Converter (ASRC)
- Human-Machine Interface (HMI)
 - GPIO pins with interrupt support, DMA request capability, digital glitch filter.
 - Hysteresis and configurable pull up/down device on all input pins
 - Configurable slew rate and drive strength on all output pins
- On-Chip Memory
 - 512 KB On-chip SRAM with ECC
 - 1 MB On-chip graphics SRAM (no ECC). This depends on the part selected. Alternate configuration could be 512 KB graphics and 512 KB L2 cache.
 - 96 KB Boot ROM

Table of Contents

1	Ordering parts.....	5	6.2.5	USB PHY current consumption.....	21
1.1	Determining valid orderable parts	5	6.2.5.1	Power Down Mode.....	21
2	Part identification.....	5	6.2.6	EMC radiated emissions operating behaviors.....	21
2.1	Description.....	5	6.2.7	EMC Radiated Emissions Web Search Procedure boilerplate.....	22
2.2	Part Number Format.....	5	6.2.8	Capacitance attributes.....	22
2.3	Fields.....	6	7	I/O parameters.....	22
2.4	Part Numbers	7	7.1	GPIO parameters.....	22
3	Terminology and guidelines.....	8	7.1.1	Output Buffer Impedance measurement.....	24
3.1	Definition: Operating requirement.....	8	7.2	DDR parameters.....	25
3.2	Definition: Operating behavior.....	8	8	Power supplies and sequencing.....	28
3.3	Definition: Attribute.....	8	8.1	Power sequencing	28
3.4	Definition: Rating.....	9	8.2	Power supply.....	30
3.5	Result of exceeding a rating.....	9	8.3	Absolute maximum ratings.....	31
3.6	Relationship between ratings and operating requirements.....	10	8.4	Recommended operating conditions.....	32
3.7	Guidelines for ratings and operating requirements.....	10	8.5	Recommended Connections for Unused Analog Interfaces...	33
3.8	Definition: Typical value.....	10	9	Peripheral operating requirements and behaviours.....	34
3.9	Typical Value Conditions.....	11	9.1	Analog.....	34
4	Handling ratings.....	12	9.1.1	12-bit ADC electrical characteristics.....	34
4.1	ESD handling ratings	12	9.1.1.1	12-bit ADC operating conditions.....	34
4.2	Thermal handling ratings.....	12	9.1.1.2	12-bit ADC characteristics.....	35
4.3	Moisture handling ratings.....	12	9.1.2	12-bit DAC electrical characteristics.....	39
5	Operating Requirements.....	13	9.1.2.1	12-bit DAC operating requirements...	39
5.1	Thermal operating requirements.....	13	9.1.2.2	12-bit DAC operating behaviors.....	39
6	General.....	13	9.1.3	VideoADC Specifications.....	43
6.1	AC electrical characteristics.....	13	9.2	Display and Video interfaces.....	45
6.2	Nonswitching electrical specifications	14	9.2.1	DCU Switching Specifications.....	45
6.2.1	VREG electrical specifications	14	9.2.1.1	Interface to TFT panels (DCU0/1).....	45
6.2.1.1	HPREG electrical characteristics.....	14	9.2.1.2	Interface to TFT LCD Panels—Pixel Level Timings.....	46
6.2.1.2	LPREG electrical characteristics.....	14	9.2.1.3	Interface to TFT LCD panels—access level.....	47
6.2.1.3	ULPREG electrical characteristics.....	15	9.2.2	Video Input Unit timing.....	48
6.2.1.4	WBREG electrical characteristics.....	15	9.2.3	LCD driver electrical characteristics.....	49
6.2.1.5	External NPN Ballast.....	16	9.3	Ethernet specifications.....	49
6.2.2	LVD electrical specifications	18	9.3.1	Ethernet Switching Specifications.....	49
6.2.2.1	Main Supply electrical characteristics	18	9.3.2	Receive and Transmit signal timing specifications	49
6.2.2.2	LVD DIG characteristics.....	18	9.3.3	Receive and Transmit signal timing specifications for MII interfaces.....	51
6.2.3	LDO electrical specifications	19	9.4	Audio interfaces.....	53
6.2.3.1	LDO_1P1.....	19			
6.2.3.2	LDO_2P5.....	19			
6.2.3.3	LDO_3P0	20			
6.2.4	Power consumption operating behaviors.....	20			

9.4.1	Enhanced Serial Audio Interface (ESAI) Timing Parameters.....	53	9.7.4	Slow internal RC oscillator (128 KHz) electrical characteristics.....	84
9.4.2	SPDIF Timing Parameters.....	55	9.7.5	PLL1 and PLL2 (528 MHz System PLL) Electrical Parameters.....	84
9.4.3	SAI/I2S Switching Specifications.....	56	9.7.6	PLL3 and PLL7 (480 MHz USB PLL) Electrical Parameters.....	84
9.5	Memory interfaces.....	58	9.7.7	PLL5 (Ethernet PLL) Electrical Parameters.....	85
9.5.1	QuadSPI timing.....	58	9.7.8	PLL4 (Audio PLL) Electrical Parameters.....	85
9.5.2	NFC specifications.....	61	9.7.9	PLL6 (Video PLL) Electrical Parameters.....	85
9.5.3	FlexBus timing specifications.....	64	9.8	Debug specifications.....	86
9.5.4	DDR controller specifications.....	66	9.8.1	JTAG electricals.....	86
9.5.4.1	DDR3 Timing Parameters	66	9.8.2	Debug trace timing specifications.....	88
9.5.4.2	DDR3 Read Cycle.....	68	10	Thermal attributes.....	89
9.5.4.3	DDR3 Write cycle.....	69	10.1	Thermal attributes.....	89
9.5.4.4	LPDDR2 Timing Parameter.....	70	11	Dimensions.....	90
9.5.4.5	LPDDR2 Read Cycle.....	71	11.1	Obtaining package dimensions	90
9.5.4.6	LPDDR2 Write Cycle.....	72	12	Pinouts.....	91
9.6	Communication interfaces.....	73	12.1	Pinouts.....	91
9.6.1	MediaLB (MLB) DC Characteristics.....	73	12.2	Pinout diagrams.....	103
9.6.2	MediaLB (MLB) Controller AC Timing Electrical Specifications.....	73	12.2.1	GPIO Mapping.....	105
9.6.3	DSPI timing specifications.....	75	12.2.2	Special Signal	109
9.6.4	I2C timing.....	78	13	Power Supply Pins.....	111
9.6.5	SDHC specifications.....	80	13.1	Power Supply Pins.....	111
9.6.6	USB PHY specifications.....	81	14	Functional Assignment Pins.....	112
9.7	Clocks and PLL Specifications.....	81	14.1	Functional Assignment Pins.....	112
9.7.1	24 MHz Oscillator Specifications.....	81	15	Revision History.....	121
9.7.2	32 KHz Oscillator Specifications.....	82			
9.7.3	Fast internal RC oscillator (24 MHz) electrical characteristics.....	83			

1 Ordering parts

1.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web.

1. To determine the orderable part numbers for this device, go to www.freescale.com and search the required part number. The part numbering format is described in the section that follows.

2 Part identification

2.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

2.2 Part Number Format

The figure below represents the format of part number of this device.

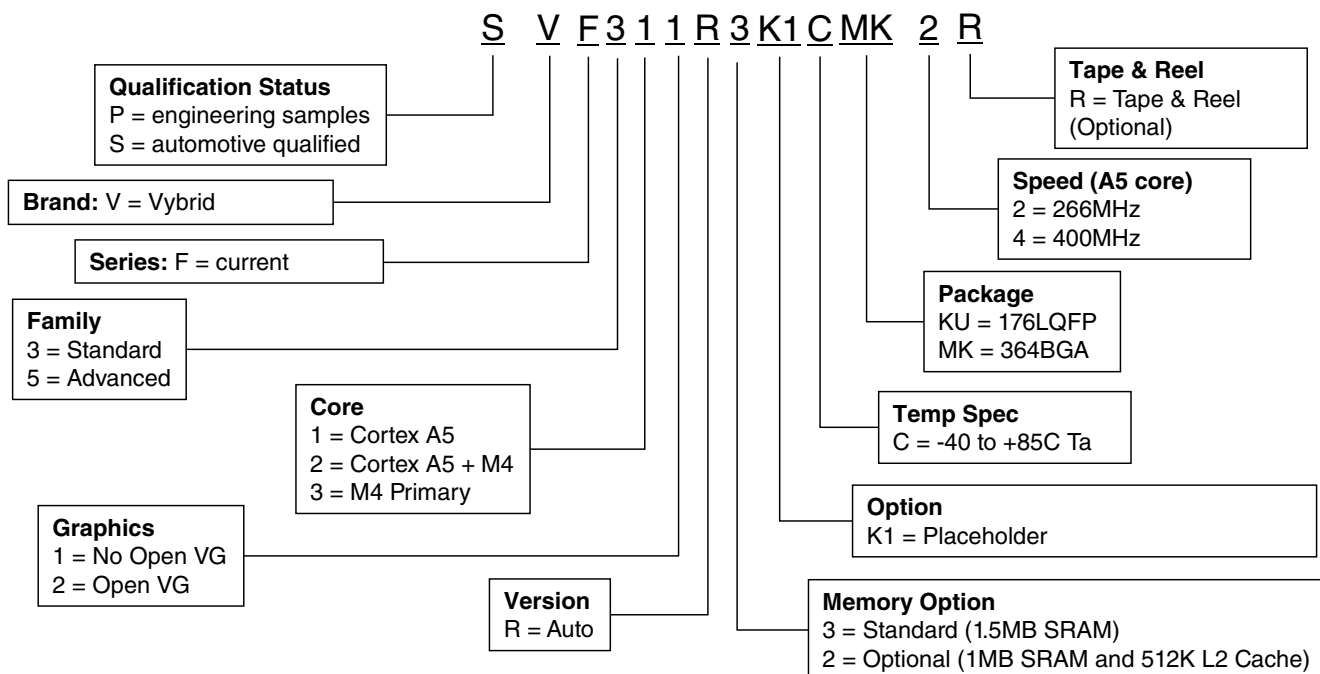


Figure 1. Part Number Format

2.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
Q	Qualification status	<ul style="list-style-type: none"> P = engineering samples S = automotive qualified
B	Brand	<ul style="list-style-type: none"> V = Vybrid
S	Series	<ul style="list-style-type: none"> F = current
F	Family	<ul style="list-style-type: none"> 3 = Standard 5 = Advanced
C	Core	<ul style="list-style-type: none"> 1 = Cortex A5 2 = Cortex A5 + M4 3 = M4 Primary
G	Graphics	<ul style="list-style-type: none"> 1 = No Open VG 2 = OpenVG
V	Version	<ul style="list-style-type: none"> R = Auto

Table continues on the next page...

Field	Description	Values
M	Memory option	<ul style="list-style-type: none"> • 3 = Standard (1.5MB SRAM) • 2 = Optional (1MB SRAM and 512K L2 Cache)
T	Temperature spec	<ul style="list-style-type: none"> • C = -40 °C to +85 °C T_a
P	Package	<ul style="list-style-type: none"> • KU = 176LQFP • MK = 364BGA
S	Speed (A5 core)	<ul style="list-style-type: none"> • 2 = 266MHz • 4 = 400MHz

2.4 Part Numbers

This table lists the part numbers on the device.

Part Number	Package	Description
SVF311R3K1CKU2	LQFP-EP 176 24*24*1.6	A5-266, 176LQFP-EP
SVF312R3K1CKU2	LQFP-EP 176 24*24*1.6	A5-266, OpenVG GPU, 176LQFP-EP
SVF321R3K1CKU2	LQFP-EP 176 24*24*1.6	A5-266, M4, 176LQFP-EP
SVF322R3K1CKU2	LQFP-EP 176 24*24*1.6	A5-266, M4, OpenVG GPU, 176LQFP-EP
SVF331R3K1CKU2	LQFP-EP 176 24*24*1.6	A5-266, M4 Primary, 176LQFP-EP
SVF332R3K1CKU2	LQFP-EP 176 24*24*1.6	A5-266, M4 Primary, OpenVG GPU, 176LQFP-EP
SVF511R3K1CMK4	MAP 364 17*17*1.5 P0.8	A5-400, 364BGA
SVF512R3K1CMK4	MAP 364 17*17*1.5 P0.8	A5-400, OpenVG GPU, 364BGA
SVF521R3K1CMK4	MAP 364 17*17*1.5 P0.8	A5-400, M4, 364BGA
SVF522R2K1CMK4	MAP 364 17*17*1.5 P0.8	A5-400, M4, L2 Cache, OpenVG GPU, 364BGA
SVF522R3K1CMK4	MAP 364 17*17*1.5 P0.8	A5-400, M4, OpenVG GPU, 364BGA
SVF531R3K1CMK4	MAP 364 17*17*1.5 P0.8	A5-400, M4 Primary, 364BGA
SVF532R2K1CMK4	MAP 364 17*17*1.5 P0.8	A5-400, M4 Primary, L2 Cache OpenVG GPU, 364BGA
SVF532R3K1CMK4	MAP 364 17*17*1.5 P0.8	A5-400, M4 Primary, OpenVG GPU, 364BGA

3 Terminology and guidelines

3.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

3.1.1 Example

This is an example of an operating requirement:

Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	0.9	1.1	V

3.2 Definition: Operating behavior

Unless otherwise specified, an *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

3.2.1 Example

This is an example of an operating behavior:

Symbol	Description	Min.	Max.	Unit
I_{WP}	Digital I/O weak pullup/pulldown current	10	130	μA

3.3 Definition: Attribute

An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

3.3.1 Example

This is an example of an attribute:

Symbol	Description	Min.	Max.	Unit
CIN_D	Input capacitance: digital pins	—	7	pF

3.4 Definition: Rating

A *rating* is a minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

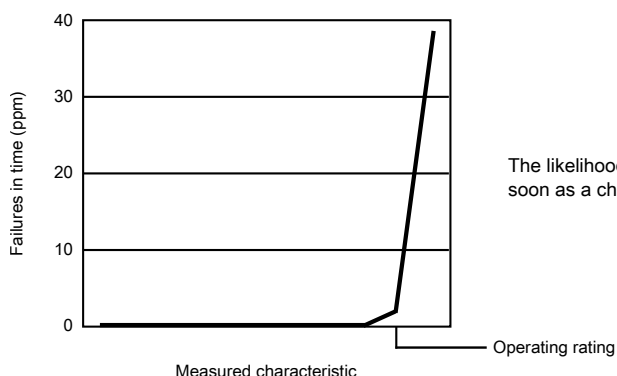
- *Operating ratings* apply during operation of the chip.
- *Handling ratings* apply when the chip is not powered.

3.4.1 Example

This is an example of an operating rating:

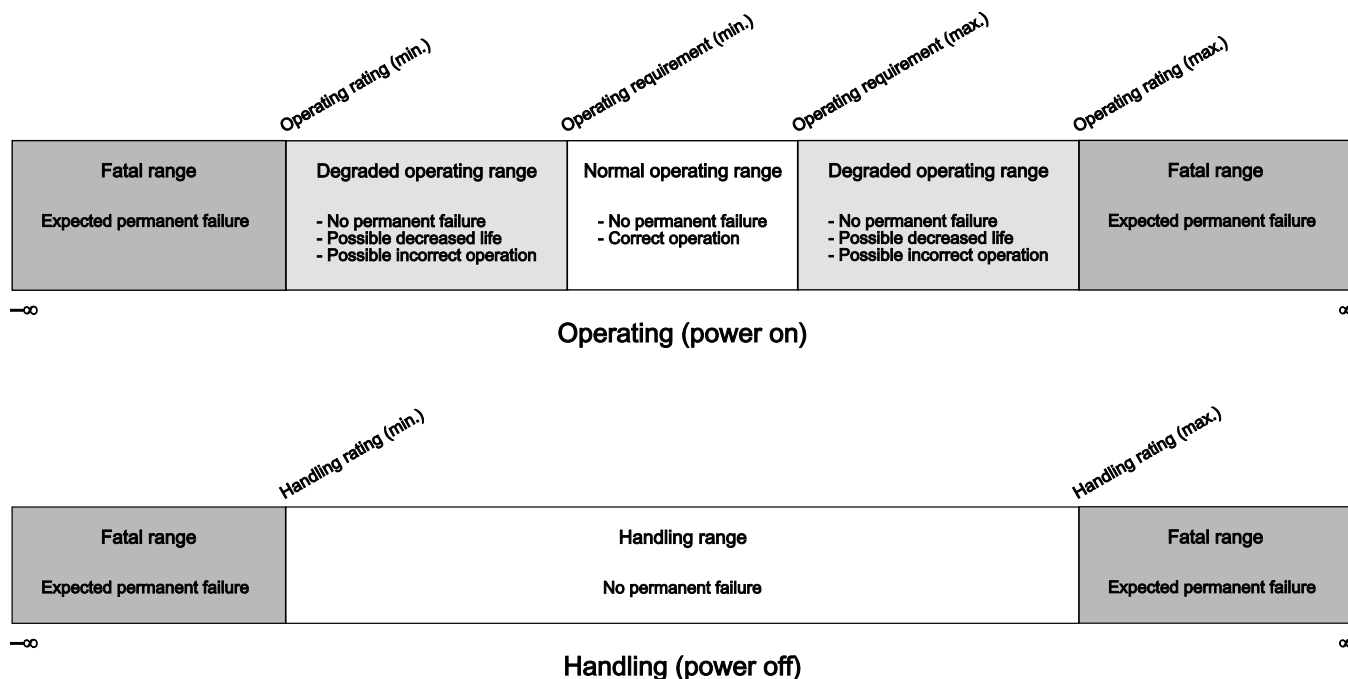
Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	-0.3	1.2	V

3.5 Result of exceeding a rating



The likelihood of permanent chip failure increases rapidly as soon as a characteristic begins to exceed one of its operating ratings.

3.6 Relationship between ratings and operating requirements



3.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

3.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

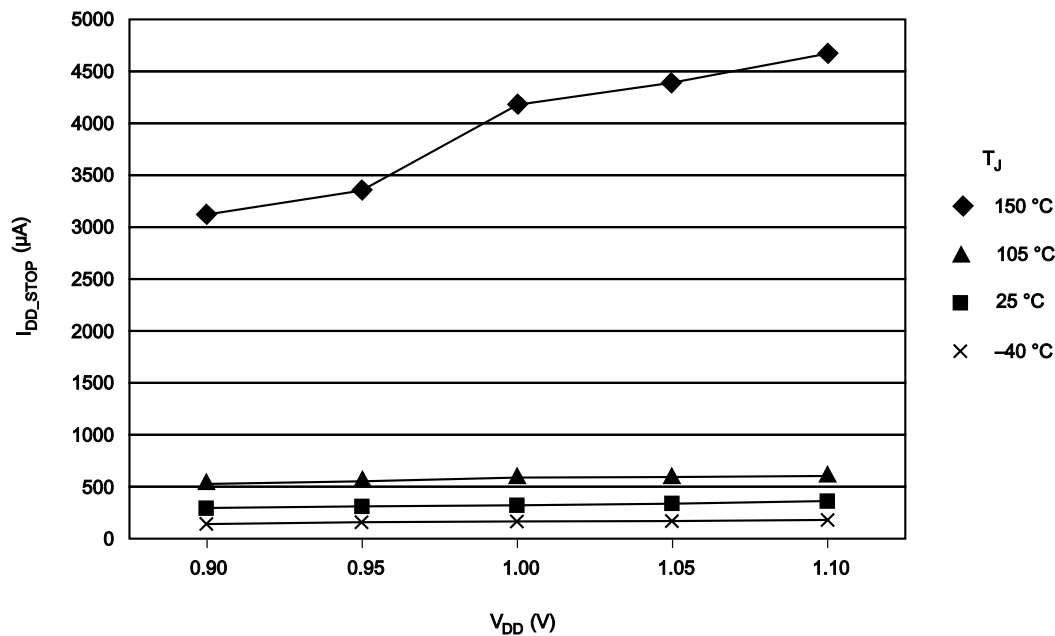
3.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Typ.	Max.	Unit
I_{WP}	Digital I/O weak pullup/pulldown current	10	70	130	μA

3.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:



3.9 Typical Value Conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Symbol	Description	Value	Unit
T_A	Ambient temperature	25	$^{\circ}\text{C}$
V_{DD}	3.3 V supply voltage	3.3	V

4 Handling ratings

4.1 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V _{HBM}	Electrostatic discharge voltage, human body model	-2000	2000	V	1
V _{CDM}	Electrostatic discharge voltage, charged-device model	-500	500	V	2
I _{LAT}	Latch-up Current at ambient temperature of 85 °C	-100	100	mA	

1. Determined according to the AEC spec AEC-Q100-002 for HBM
2. Determined according to AEC spec AEC-Q100-011

4.2 Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T _{STG}	Storage temperature	-55	150	°C	1
T _{SDR}	Solder temperature, lead-free	—	260	°C	2
	Solder temperature, leaded	—	245		

1. Determined according to JEDEC Standard JESD22-A103, *High Temperature Storage Life*.
2. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.3 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

5 Operating Requirements

5.1 Thermal operating requirements

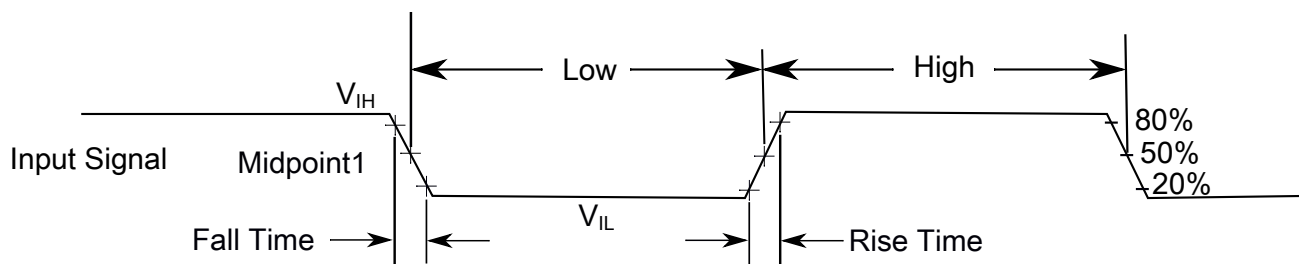
Table 1. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
T_A	Ambient temperature	-40	85	°C
T_J	Junction temperature		105	°C

6 General

6.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.



The midpoint is $V_{IL} + (V_{IH} - V_{IL}) / 2$

Figure 2. Input signal measurement reference

6.2 Nonswitching electrical specifications

6.2.1 VREG electrical specifications

6.2.1.1 HPREG electrical characteristics

Table 2. HPREG electrical characteristics

Parameters	Min	Typ	Max	Unit	Comments
Power supply	3.0	3.3	3.6	V	-
Current Consumption	-	1.2	1.5	mA	@ no load
	-	2.0	2.5	mA	@ full load
Output current capacity	-	600	1200 ¹	mA	DC load current
Output voltage @ no load		1.23	1.26	V	
Output voltage @ full load	1.20	1.21		V	
External decoupling cap	4.7		-	μF	-
	0.05		0.1	Ohms	ESR of external cap
			20	mOhms	Total effective PAD+PCB trace resistances
PSRR with 4.7μF output cap					
@ DC @noload			-48	dB	
@ DC @full load			-40		
@ worst case any frequency			-20		

1. This is peak and not continuous maximum value.

6.2.1.2 LPREG electrical characteristics

Table 3. LPREG electrical characteristics

Parameters	Min	Typ	Max	Unit	Comments
Power supply	3.0	3.3	3.6	V	
Current Consumption	350	400		μA	@ no load
	-	500	650	μA	@ full load
Output current capacity		100	200	mA	DC load current
Output voltage @ no load		1.22	1.240	V	
Output voltage @ full load	1.180			V	
External decoupling cap	4.7			μF	
	0.05		0.1	Ohms	ESR of external cap
			20	mOhms	Total PAD+PCB trace resistance

Table continues on the next page...

**Table 3. LPREG electrical characteristics
(continued)**

Parameters	Min	Typ	Max	Unit	Comments
PSRR with 4.7uF output cap					
@ DC @noload			-40	dB	
@ DC @full load			-35		
Worst case @ any frequency			-12		

6.2.1.3 ULPREG electrical characteristics

Table 4. ULPREG electrical characteristics

Parameters	Min	Typ	Max	Unit	Comments
Power supply	3.0	3.3	3.6	V	
Current Consumption	1.88	2.3	2.86	μA	@ no load
	-	610	670	μA	@ full load
Output current capacity			20	mA	DC load current
Output voltage @ no load			1.175	V	
Output voltage @ full load	1.125			V	
PSRR with 500 pF output cap	-20			dB	Worst case at any frequency across corners
@ DC @noload			-50	dB	
@200KHz @noload			-37		
@ DC @full load			-42		
@200KHz @full load			-37		
Worst case @ any frequency @ any load			-15		

6.2.1.4 WBREG electrical characteristics

Table 5. WBREG electrical characteristics

Parameters	Min	Typ	Max	Unit	Comments
Power supply	3	3.3	3.6	V	-
Current Consumption	-	2	5	μA	@ no load
	-	2	5	μA	@ full load
Output current capacity	-	1	2	mA	DC load current
Output voltage @ no load		1.4	1.425	V	
Output voltage @ full load	1.375	1.398		V	
Output voltage programmability	1.4	1.4	1.7	V	16 steps of 25 mV each

6.2.1.5 External NPN Ballast

The internal main regulator requires an external NPN ballast transistor to be connected as shown in the following figure as well as an external capacitance to be connected to the device in order to provide a stable 1.2V digital supply to the device. The HPREG design allows for collector voltage lower than VDDREG value. See AN4807 at www.freescale.com.

NOTE

To not overload BCTRL output, collector voltage should appear no later than $VDDREG / VDD33$ (3.3V).

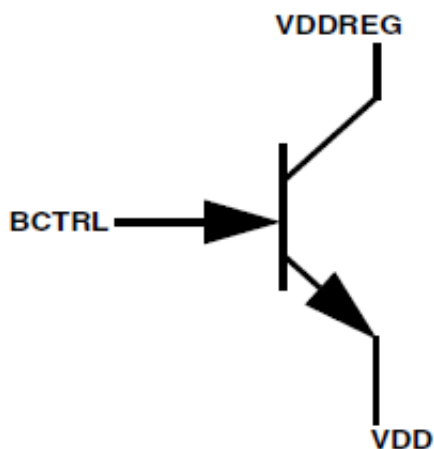


Figure 3. External NPN Ballast connections

Table 6. BCTRL OUTPUT specification

Parameter	Value	Comments
BCTRL OUTPUT specification	20mA	BCTRL driver can not drive more than 20mA current
Maximum pin voltage	$VDDREG - 0.5V$	For Example, $VDDREG = 3.0V$ BCTRL should not exceed 2.5V.

Table 7. Assumptions For calculations

Parameter	Value
VDDREG	3.0V to 3.6V with typical value of 3.3V
Max DC Collector current	0.85A @ 85 °C
Emitter voltage	1.2V to 1.25V
Collector voltage	Equal to VDDREG

Table 8. General guidelines for selection of NPN ballast

Symbol	Parameters	Value	Unit	Comments
Hfe	Minimum DC current gain (Beta)	42.5		As BCTRL pin can not drive more than 20mA Minimum value of beta for a collector current of 0.85A comes out to be 42.5.
PD (Junction to ambient)	Minimum power dissipation @ TA=85 °C	2.04	W	Assuming 0.85A collector current with Collector voltage of Ballast 3.6V(max) we get VCE= 3.6V-1.2V=2.4V So power dissipated is 2.4V*0.85A=2.04W . This should be met for junction to ambient power dissipation spec of ballast
IcmaxDC peak	Maximum peak DC collector current	0.85	A	1.2A and above capacity device preferable
VBE	Maximum voltage that BCTRL pin can drive	1.25V for 0.85A @ 85 °C	V	For a VDDREG of 3.0 V (min.), BCTRL pin can drive voltage up to VDDREG - 0.5 V = 2.5 V. Since emitter of ballast is fixed at 1.25 V (max) if chosen ballast can supply 0.85 A collector current @ 85 °C with a base-to-emitter voltage of 1.25 V or lower, it is suitable for application.
Ft	Unity current gain Frequency of Ballast	50	MHz	

Reducing the collector-to-emitter voltage drop lowers the ballast transistor heat dissipation. This can be implemented in two ways:

1. By introducing series resistor or diode(s) between the collector and VDDREG (placed far enough from the transistor for proper cooling)
2. By connecting the collector to a separate lower-voltage supply

In both of the above cases the transistor has to stay away from the deep saturation region; otherwise, due to significant Hfe degradation, its base current exceeds the BCTRL output maximum value.

In general, the transistor must be selected such that its Vce saturation voltage is lower than the expected minimum Collector-Emitter voltage, and at the same time, the base current is less than 20 mA for the maximum expected collector current. More information can be found in collateral documentation at <http://www.freescale.com>

6.2.2 LVD electrical specifications

6.2.2.1 Main Supply electrical characteristics

Table 9. LVD_MAIN supply electrical characteristics

Main Supply LVD Parameters	Min	Typ	Max	Unit	Comments
Power supply	3.0	3.3	3.6	V	
Upper voltage threshold (value @27°C)		2.76	2.915	V	
Lower voltage threshold (value @27°C)	2.656	2.73		V	
Time constant of RC filter at LVD input (0.69*RC)	3.3			µs	3.3 V noise rejection at LVD comparator input

6.2.2.2 LVD DIG characteristics

Table 10. LVD DIG electrical specifications [HPREG(RUN MODE) and LPREG(STOP MODE)]

LVD DIG Parameters	Min	Typ	Max	Unit	Comments
Power supply	3.0	3.3	3.6	V	
Upper voltage threshold	1.135	1.16	1.185	V	
Lower voltage threshold	1.105	1.13	1.155	V	
Time constant of RC filter at LVD input	200			ns	1.2V noise rejection at the input of LVD comparator

Table 11. LVD DIG electrical specifications [ULPREG(STANDBY MODE)]

LVD DIG Parameters	Min	Typ	Max	Unit	Comments
Power supply	3.0	3.3	3.6	V	
Upper voltage threshold	1.105	1.13	1.155	V	
Lower voltage threshold	1.075	1.10	1.125	V	
Time constant of RC filter at LVD input	200			ns	1.2V noise rejection at the input of LVD comparator

6.2.3 LDO electrical specifications

6.2.3.1 LDO_1P1

Table 12. LDO_1P1 parameters

Specification	Min	Typ	Max	Unit	Comments
VDDIO	3	3.3	3.6	V	IO supply
VDD1P1_OUT	0.9	1.1	1.2	V	Regulator output
I _{out}	-		150	mA	>= 300mV drop out
Regulator output programming range	0.8	1.1	1.4	V	Programmable in 25mV steps
Brownout Voltage	0.85	0.94		V	
Brownout offset step	0	-	175	mV	Programmable in 25mV steps
Minimum external decoupling capacitor	1	-	-	μF	low ESR

For additional information, see the device reference manual.

6.2.3.2 LDO_2P5

Table 13. LDO_2P5 parameters

Specification	Min	Typ	Max	Unit	Comments
VDDIO	3	3.3	3.6	V	IO supply
VDD2P5_OUT	2.3	2.5	2.6	V	Regulator output
I _{out}	-		350	mA	@500mV drop out
Regulator output programming range	2.0	2.5	2.75	V	Programmable in 25mV steps
[P:][C:] Brownout Voltage	2.25	2.33		V	
Brownout offset step	0	-	175	mV	Programmable in 25mV steps
Minimum external decoupling capacitor	1	-	-	μF	low ESR

For additional information, see the reference manual.

6.2.3.3 LDO_3P0

Table 14. LDO_3P0 parameters

Specification	Min	Typ	Max	Unit	Comments
Input OTG VBUS Supply	4.4		5.25	V	
Input HOST VBUS Supply	4.4		5.25	V	
VDD3P0_OUT	2.9	3.0	3.1	V	Regulator output at default setting
I_out	-		50	mA	500 mV drop-out voltage
Regulator output programming range	2.625		3.4	V	Programmable in 25mV steps
[P:][C:] Brownout Voltage	2.75	2.85		V	
Brownout offset step	0	-	175	mV	Programmable in 25mV steps
Minimum external decoupling capacitor	1	-	-	μF	low ESR

NOTE

These values are with Anadig_REG_3P0[ENABLE_ILIMIT]= 0 and Anadig_REG_3P0[ENABLE_LINREG]= 1. It is required to set these values before using USB.

6.2.4 Power consumption operating behaviors

Table 15. Power consumption operating behaviors

Symbol	Description	Typ. ¹	Max. ²	Unit	Notes
I _{DD_RUN}	Run mode current — All functionalities of the chip available	400	850	mA	
I _{DD_WAIT}	Wait mode high frequency current at 3.3 V ± 10%	80	500	mA	3
I _{DD_LPRUN}	Low-power run mode current at 3.3 V ± 10%, 24MHz operation, PLL Bypass.	13	325	mA	4
I _{DD_ULPRUN}	Ultra-low-power run mode current at 3.3 V ± 10%	12	395	mA	5
I _{DD_STOP}	Stop mode current at 3.3 V ± 10%	7	300	mA	6
I _{DD_LPS3}	Low-power stop3 mode current at 3.3 V ± 10%	300	1300	uA	7
I _{DD_LPS2}	Low-power stop 2 mode current at 3.3 V ± 10%	50	875	uA	8
I _{DD_VBAT}	Battery backup mode	5	45	uA	9

1. The Typ numbers represent the average value taken from a matrix lot of parts across normal process variation at ambient temperature.

2. The Max numbers represent the single worst case value taken from a matrix lot of parts across normal process variation at maximum temperature.
3. CA5, CM4 cores halted
4. 24MHz operation, PLL Bypass
5. 32 kHz /128 kHz operation, PLL Off
6. Lowest power mode with all power retained, RAM retention and LVD protection.
7. Standby Mode. 64K RAM retention. I/O states held. ADCs/DACs optionally power-gated. RTC functional. Wakeup from interrupts. Fast IRC enabled.
8. Standby Mode 16K RAM retention. I/O states held. ADCs/DACs optionally power-gated. RTC functional. Wakeup from interrupts. Fast IRC enabled.
9. All supplies OFF, SRTC, 32kXOSC ON, tampers and monitors ON. 128k IRC optionally ON.

6.2.5 USB PHY current consumption

6.2.5.1 Power Down Mode

Everything powered down, including the VBUS valid detectors, typ condition.

Table 16. USB PHY Current Consumption in Normal Mode

	USBx_VBUS (3.0V) Avg	VDD33_LDOIN (2.5V) Avg	VDD33_LDOIN (1.1V) Avg
Current	5.1 μ A	1.7 μ A	<0.5 μ A

NOTE

The currents on the 2.5 voltage regulator and 3.0 voltage regulator were identified to be the voltage divider circuits in the USB-specific level shifters.

6.2.6 EMC radiated emissions operating behaviors

Table 17. EMC radiated emissions operating behaviors

Symbol	Condition ¹	Clocks	Frequency band ²	Level (Typ) ³	Unit
V _{EME}	Device Configuration, test conditions and EM testing per standard IEC 61967-2; Supply voltages: VDD= 5.0 V VDD33 = 3.3 V VDD15 = 1.5 V VDD12 = 1.2 V Temp = 25°C	FCPU = 396 MHz FBUS = 66 MHz External Crystal = 24 MHz	150 KHz – 50 MHz	22	dB μ V
			50 MHz – 150 MHz	24	
			150 MHz – 500 MHz	25	
			500–1000	20	
			IEC level ⁴	K	—

1. Measurements were made per IEC 61967-2 while the device was running basic application code.
2. Measurements were performed on the BGA364 version of the device

I/O parameters

- The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.
- IEC Level Maximums: N ≤ 12dBmV, M ≤ 18dBmV, L ≤ 24dBmV, K ≤ 30dBmV, I ≤ 36dBmV, H ≤ 42dBmV

6.2.7 EMC Radiated Emissions Web Search Procedure boilerplate

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

- Go to www.freescale.com.
- Perform a keyword search for “EMC design.”

6.2.8 Capacitance attributes

Table 18. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C _{IN_A}	Input capacitance: analog pins	—	7	pF
C _{IN_D}	Input capacitance: digital pins	—	7	pF

7 I/O parameters

7.1 GPIO parameters

Table 19. GPIO DC operating conditions

Symbol	Parameter	Min	Typ	Max	Unit
vddi ¹	Core internal supply voltage		1.2		V
ovdd	I/O output supply voltage	3	3.3	3.6	V

- This is internally controlled.

Table 20. GPIO DC Electrical characteristics

Symbol	Parameter	Test condition	Min	Typ	Max	Unit
V _{oh}	High-level output voltage	I _{oh} = -1mA	ovdd-0.15			V

Table continues on the next page...

Table 20. GPIO DC Electrical characteristics (continued)

Symbol	Parameter	Test condition	Min	Typ	Max	Unit
		VOH/VOL values are with respect to DSE=001 ¹				
V _{ol}	Low-level output voltage	I _{ol} = 1mA			0.15	V
V _{ih}	High-Level DC input voltage		0.7*ovdd		ovdd	V
V _{il} ²	Low-Level DC input voltage		0		0.3*ovdd	V
V _{hys}	Input Hysteresis	ovdd=3.3 V	250			mV
V _{t+} ²	Schmitt trigger VT+		0.5*ovdd			V
V _{t-} ^{2, 3}	Schmitt trigger VT-				0.5*ovdd	V
I _{in} ⁴	Input current (no pull-up/down)	V _{in} = ovdd or 0	-1		1	uA
I _{in_22pu}	Input current (22KOhm PU)	V _{in} = 0			212	uA
		V _{in} = ovdd			1	
I _{in_47pu}	Input current (47KOhm PU)	V _{in} = 0			100	
		V _{in} = ovdd			1	
I _{in_100pu}	Input current (100KOhm PU)	V _{in} = 0			50	
		V _{in} = ovdd			1	
I _{in_100pd}	Input current (100KOhm PD)	V _{in} = 0			1	50
		V _{in} = ovdd				
R_Keeper	Keeper Circuit Resistance	V _{in} = 0.3 x OVDD V _I = 0.7 x OVDD	105		175	Ohm
I _{ssod}	Sink current in open drain mode	V _{in} = ovdd			7	mA
I _{ssop}	Sink/source current in Push Pull mode	V _{in} = ovdd			7	mA

- For details about Software MUX Pad Control Register DSE bit, see IOMUX Controller chapter of the device reference manual.
- To maintain a valid level, the transitioning edge of the input must sustain a constant slew rate (monotonic) from the current DC level through to the target DC level, V_{IL} or V_{IH}. Monotonic input transition time is from 0.1ns to 1s. V_{il} and V_{ih} do not apply when hysteresis is enabled.
- Hysteresis of 250 mV is guaranteed over all operating conditions when hysteresis is enabled.
- Typ condition: typ model, 3.3V, and 25°C. Max condition: bcs model, 3.6V, and -40°C. Min condition: wcs model, 3.0V and 85 °C. These values are for digital IO buffer cells.

Table 21. GPIO AC Electrical Characteristics (3.3V power mode)

Symbol	Parameter	Drive strength ¹	Slew rate	Test conditions	Min	Max	Unit
tpr	IO Output Transition Times (PA1), rise/fall	Max 1 1 1	slow	15pF Clod on pad, input edge rate 200ps	1.70	1.81	ns
			fast		1.04	1.18	
		High 1 0 1	slow		2.30	2.44	
			fast		1.69	1.79	
		Medium 1 0 0	slow		3.07	3.31	
			fast		2.45	2.61	
		Low 0 1 1	slow		5.13	5.44	
			fast		4.79	5.18	
tpo	IO Output Propagation Delay (PA2), rise/fall	Max 1 1 1	slow	15pF Clod on pad, input edge rate 200ps	5.01	5.04	ns
			fast		3.06	3.10	
		High 1 0 1	slow		5.55	5.68	
			fast		3.52	3.55	
		Medium 1 0 0	slow		6.37	6.67	
			fast		4.04	4.11	
		Low 0 1 1	slow		7.39	7.60	
			fast		5.54	6.10	
tpv	Output Enable to Output Valid Delay, rise/fall	Max 1 1 1	slow	15pF Clod on pad, input edge rate 200ps, 0->1, 1->0 pad transitions	5.12	5.21	ns
			fast		3.18	3.28	
		High 1 0 1	slow		5.72	5.80	
			fast		3.67	3.71	
		Medium 1 0 0	slow		6.55	6.80	
			fast		4.06	4.09	
		Low 0 1 1	slow		7.80	8.19	
			fast		5.72	6.22	
tpi	Input Pad Propagation Delay rise/fall	without hysteresis	-	150f Clod on, input edge rate from pad =1.2ns	1.06	1.31	ns
		with hysteresis	-		1.22	1.41	

1. The drive strengths are controlled by the DSE bit of the Software MUX Pad Control Register. For details, see IOMUX Controller chapter of the device reference manual.

7.1.1 Output Buffer Impedance measurement

Table 22. Output Buffer Average Impedance (3.3V power mode)

Symbol	Parameter	Drive strength ¹	Min	Typ	Max	Unit
Rdrv	Output driver impedance	0 0 1	116	150	220	Ohm
		0 1 0	58	75	110	
		0 1 1	39	50	73	

Table continues on the next page...

Table 22. Output Buffer Average Impedance (3.3V power mode) (continued)

Symbol	Parameter	Drive strength ¹	Min	Typ	Max	Unit
		1 0 0	30	37	58	
		1 0 1	24	30	46	
		1 1 0	20	25	38	
		Extra drive strength				
		1 1 1	17	20	32	

1. The drive strengths are controlled by the DSE bit of the Software MUX Pad Control Register. For details, see IOMUX Controller chapter of the device reference manual.

7.2 DDR parameters

Table 23. DDR operating conditions

Symbol	Parameter	Min	Typ	Max	Unit
vddi	Core internal supply voltage	1.16	1.23	1.26	V
ovdd	I/O output supply voltage (DDR3 mode)	1.425	1.5	1.575	V
ovdd	I/O output supply voltage (LPDDR2 mode)	1.14	1.2	1.26	V
vdd2p5	I/O PD predriver and level shifters supply voltage	2.25	2.5	2.75	V

Table 24. LPDDR2 mode DC Electrical characteristics

Symbol	Parameter	Test condition	Min	Typ	Max	Unit	Notes
Voh	High-level output voltage		0.9*ovdd			V	Note that the JEDEC LPDDR2 specification (JESD209_2B) supersedes any specification in this document.
Vol	Low-level output voltage				0.1*ovdd	V	
Vref	Input reference voltage		0.49*ovdd	0.5*ovdd	0.51*ovdd	V	
Vih(dc)	DC input high voltage		Vref+0.13		ovdd	V	
Vil(dc)	DC input low voltage		ovss		Vref-0.13	V	
Vih(diff)	DC differential input logic high		0.26		Note ¹	V	
Vil(diff)	DC differential input logic low		Note		-0.26	V	

Table continues on the next page...